



Docket No. 8733.154.00

#9  
Makita  
8/22/01  
(NE)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICATION OF: Jin JANG et al.

GAU: 1765

SERIAL NO: 09/350,313

EXAMINER: R. Kunemund

FILING DATE: July 9, 1999

FOR:

METHOD OF CRYSTALLIZING AMORPHOUS SILICON LAYER AND  
CRYSTALLIZING APPARATUS THEREOF

RECEIVED  
AUG 22 2001  
C-700 MAIL ROOM

**REQUEST FOR RECONSIDERATION**

COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

This Request for Reconsideration is in response to the Office Action mailed on May 17, 2001.

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**REMARKS**

Claims 1-19, 22, and 24-41 are pending in the subject application. All claims stand rejected, either under 35 U.S.C. 102(a and e) as being anticipated by, or under 35 U.S.C. 103(a) as being obvious over, Makita et al. (US Patent 5,851,860). With all respect to the Examiner, the rejections of claims 1-19, 22 and 24-41 are traversed. Reconsideration and subsequent allowance of the subject application in light of the following remarks are solicited.

We plead with the Examiner to carefully review the section of Makita et al., specifically column 23, lines 18-42, that is relied upon when rejecting the pending claims. The US Patent and Trademark Office's position, that column 23, lines 18-42 discloses plasma deposition of a catalyst into exposed amorphous silicon, is incorrect.

We wish to point out that column 23, lines 18-19 begins with an introductory clause, "In the above-described two production methods developed by the present inventors, ..." That